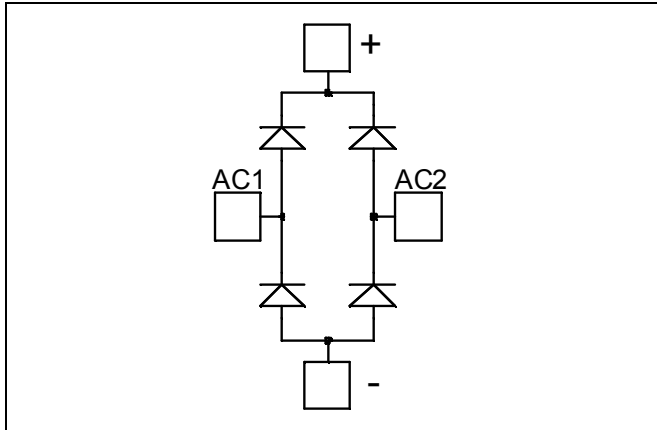


## Diode Full Bridge Power Module

$V_{RRM} = 1200V$   
 $I_C = 100A @ T_c = 60^\circ C$

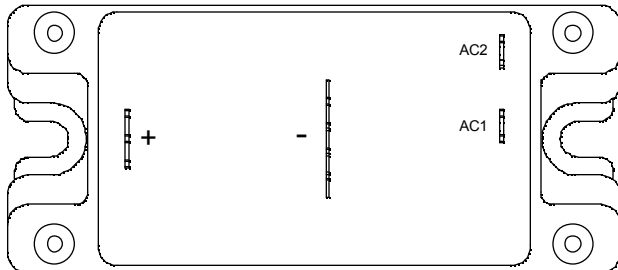


### Application

- Uninterruptible Power Supply (UPS)
- Induction heating
- Welding equipment
- High speed rectifiers

### Features

- Ultra fast recovery times
- Soft recovery characteristics
- High blocking voltage
- High current
- Low leakage current
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration




### Benefits

- Outstanding performance at high frequency operation
- Low losses
- Low noise switching
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit	
$V_R$	Maximum DC reverse Voltage	1200	V	
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			
$I_{F(AV)}$	Maximum Average Forward Current	Duty cycle = 50%	$T_C = 25^\circ C$	A
			$T_C = 60^\circ C$	
$I_{F(RMS)}$	RMS Forward Current	Duty cycle = 50%	$T_C = 45^\circ C$	
$I_{FSM}$	Non-Repetitive Forward Surge Current	8.3ms	$T_C = 45^\circ C$	

 **CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$V_F$	Diode Forward Voltage	$I_F = 100\text{A}$			2.4	3	V
		$I_F = 150\text{A}$			2.7		
		$I_F = 100\text{A}$	$T_j = 125^\circ\text{C}$		1.8		
$I_{RM}$	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$			100	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$			500	
$C_T$	Junction Capacitance	$V_R = 1200\text{V}$			110		pF

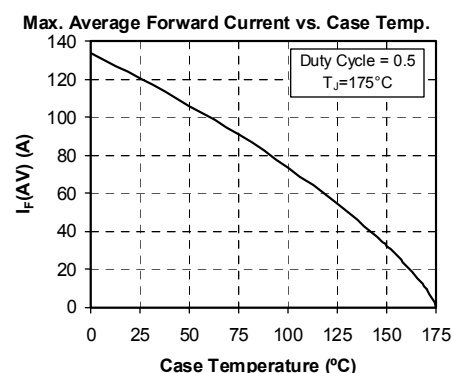
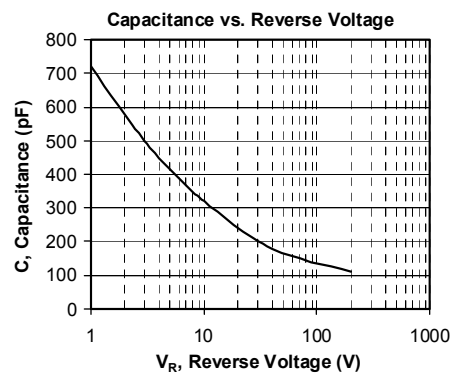
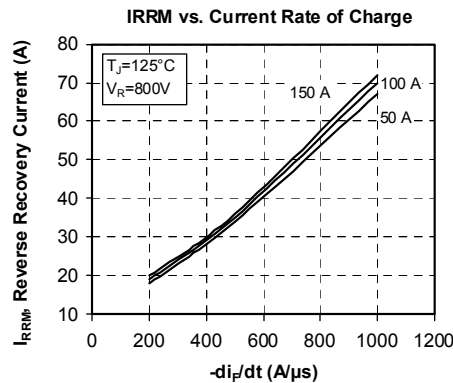
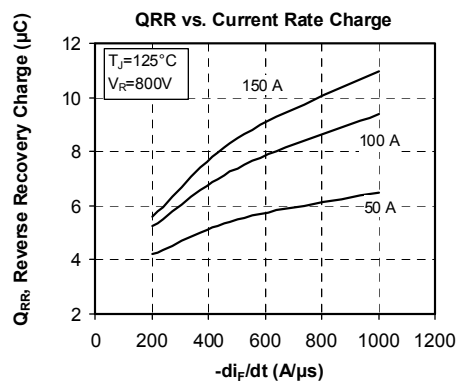
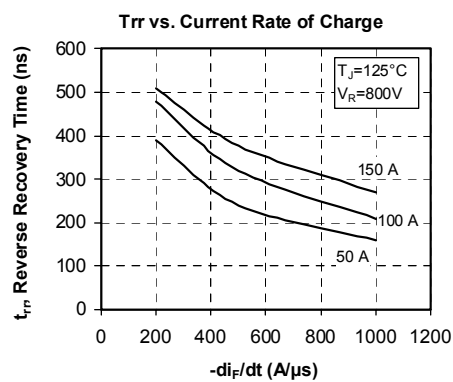
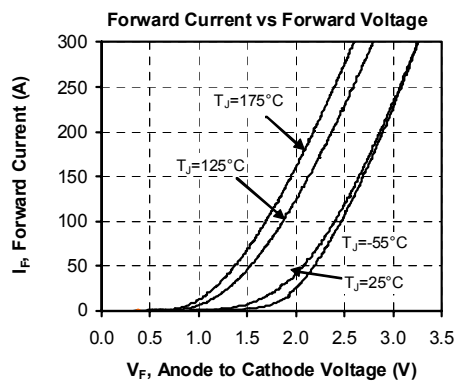
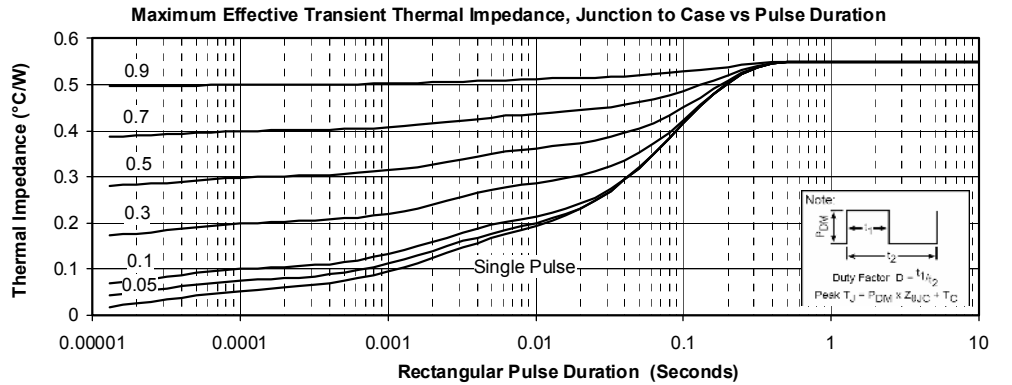
**Dynamic Characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, V_R = 30\text{V}$ $di/dt = 100\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		45		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		385		ns
			$T_j = 125^\circ\text{C}$		480		
$Q_{rr}$	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		1055		nC
			$T_j = 125^\circ\text{C}$		5240		
$I_{RRM}$	Reverse Recovery Current		$T_j = 25^\circ\text{C}$		6		A
			$T_j = 125^\circ\text{C}$		19		
$t_{rr}$	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 800\text{V}$ $di/dt = 1000\text{A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		210		ns
$Q_{rr}$	Reverse Recovery Charge				9.4		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current				70		A

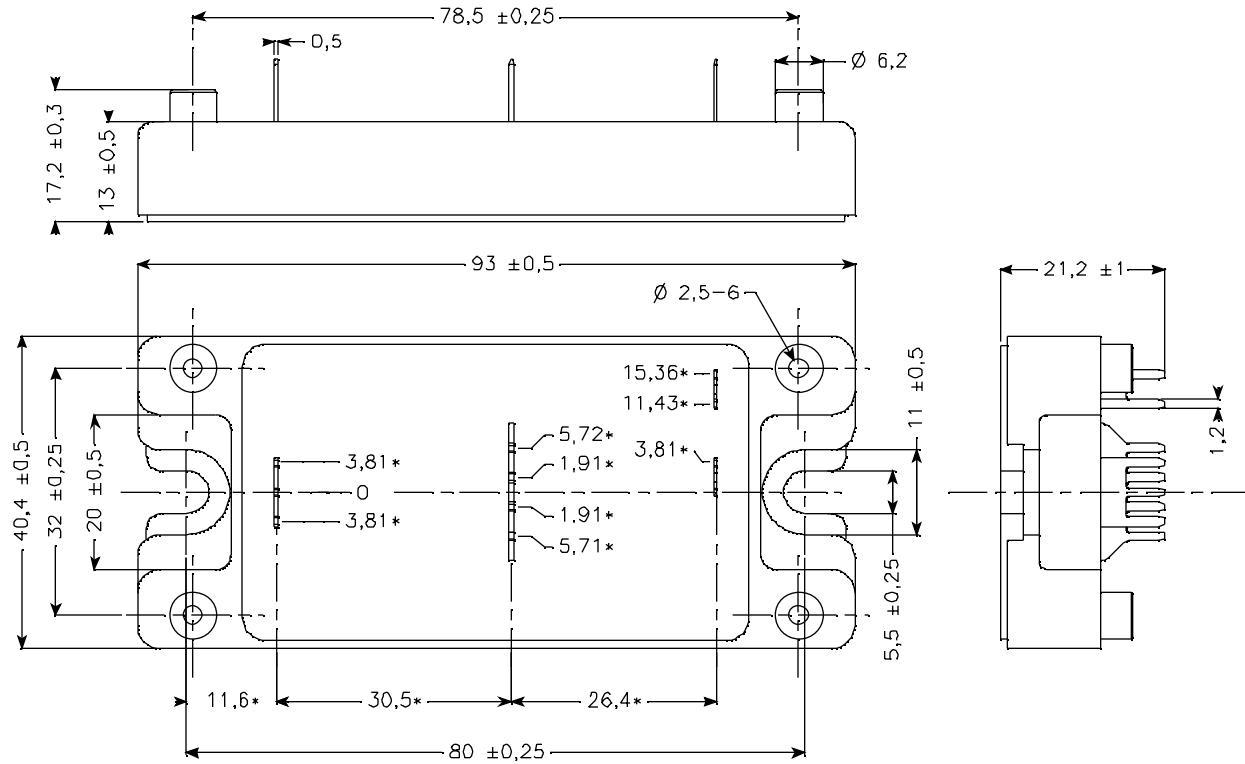
**Thermal and package characteristics**

<i>Symbol</i>	<i>Characteristic</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
$R_{thJC}$	Junction to Case Thermal Resistance			0.55	$^\circ\text{C}/\text{W}$	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t = 1\text{ min}$ , $I_{iso} < 1\text{mA}$ , 50/60Hz	2500			V	
$T_j$	Operating junction temperature range	-40		175	$^\circ\text{C}$	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

## Typical Performance Curve



## SP4 Package outline (dimensions in mm)



ALL DIMENSIONS MARKED "\*" ARE TOLERENCED AS :  $\boxed{\varnothing/\varnothing 1}$

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